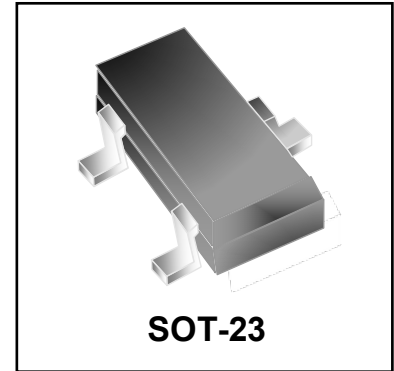


Features

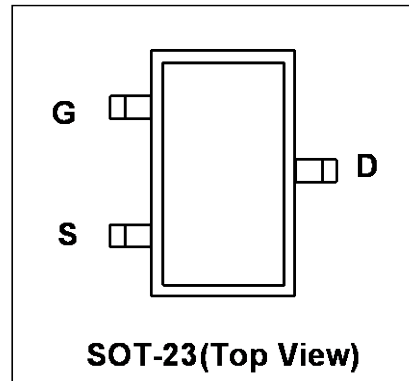
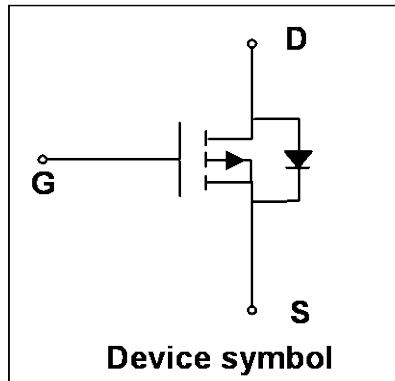
- Way-on Small Signal MOSFETs
- $V_{DS} = -30\text{ V}$, $I_D = -4.1\text{ A}$
 $R_{DS(on)} < 55\text{ m}\Omega$ @ $V_{GS} = -10\text{ V}$
 $R_{DS(on)} < 75\text{ m}\Omega$ @ $V_{GS} = -4.5\text{ V}$
- Trench LV MOSFET Technology

Mechanical Characteristics

- SOT-23 Package
- Marking : Making Code
- RoHS Compliant



Schematic & PIN Configuration



Absolute Maximum Rating ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	-4.1	A
Pulsed Drain Current ¹	I_{DM}	-25	A
Power Dissipation	P_D	1.2	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction to Ambient ²	$R_{\theta JA}$	104	$^\circ\text{C/W}$

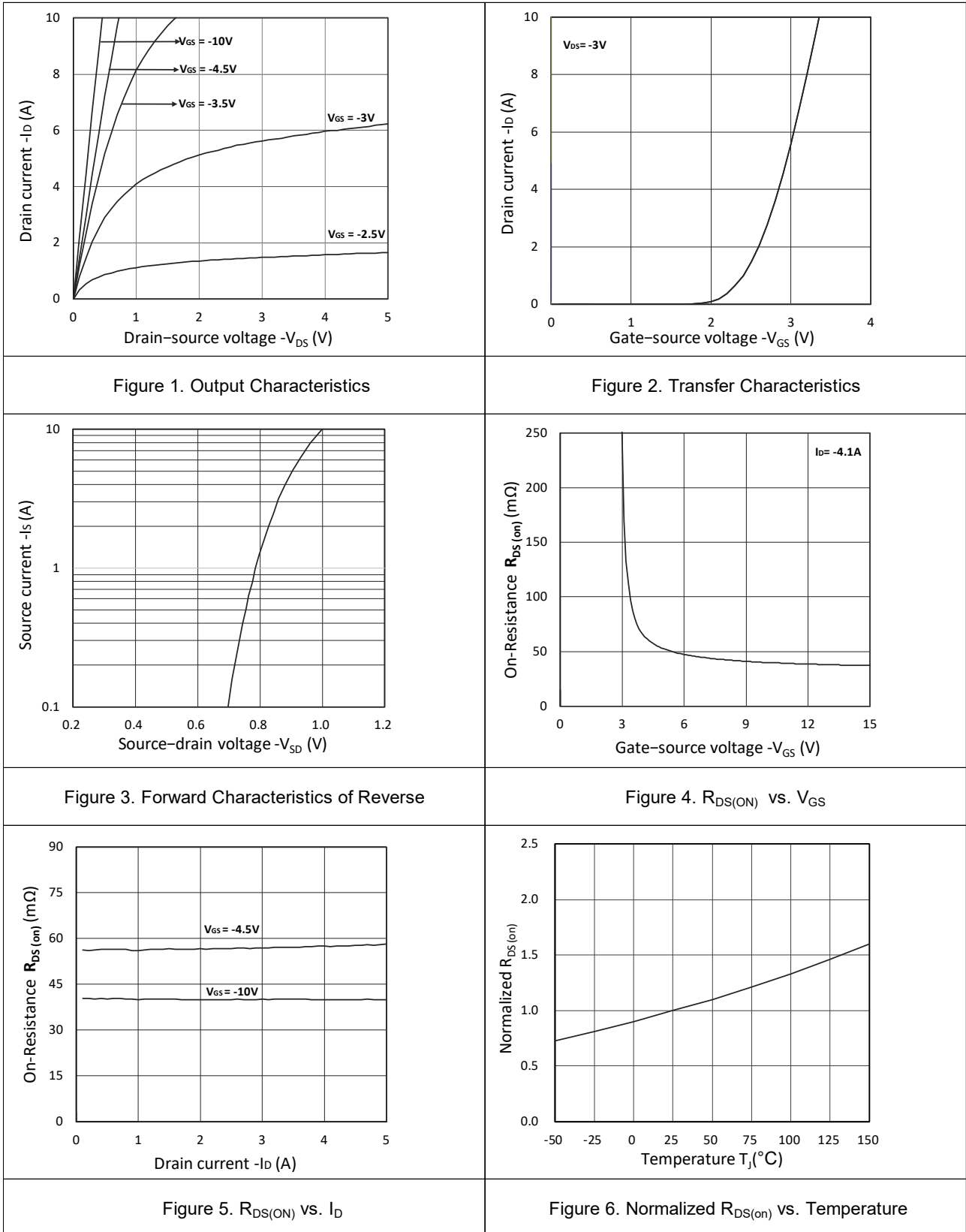
Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	V_{(BR)DSS}	V _{GS} = 0V, I _D = -250μA	-30	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V _{DS} = -30V, V _{GS} = 0V	-	-	-1	μA
Gate-Source Leakage	I_{GSS}	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA
Gate-Source Threshold voltage	V_{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA	-1	-1.5	-2.5	V
Drain-Source on-State Resistance ³	R_{DS(on)}	V _{GS} = -10V, I _D = -4.1A	-	40	55	mΩ
		V _{GS} = -4.5V, I _D = -3A	-	54	75	
Dynamic Characteristics⁴						
Input Capacitance	C_{iss}	V _{GS} = 0V , V _{DS} = -15V, f = 1MHz	-	530	-	pF
Output Capacitance	C_{oss}		-	70	-	
Reverse Transfer Capacitance	C_{rss}		-	56	-	
Switching Characteristics⁴						
Total Gate Charge	Q_g	V _{GS} = -10V, V _{DS} = -15V, I _D = -4.1A	-	6.8	-	nC
Gate-Source Charge	Q_{gs}		-	1.0	-	
Gate-Drain Charge	Q_{gd}		-	1.4	-	
Turn-on Delay Time	t_{d(on)}	V _{GS} = -10V, V _{DD} = -15V , R _G = 3Ω, I _D = -4.1A	-	14	-	ns
Rise Time	t_r		-	61	-	
Turn-off Delay time	t_{d(off)}		-	19	-	
Fall Time	t_f		-	10	-	
Source-Drain Body Diode Characteristics						
Diode Forward Voltage ³	V_{SD}	I _S = -4.1A, V _{GS} = 0V	-	-	-1.2	V
Continuous Source Current	I_S		-	-	-4.1	A

Notes:

1. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C.
2. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
3. Pulse Test: Pulse width≤300μs, duty cycle≤2%.
4. This value is guaranteed by design hence it is not included in the production test.

Typical Characteristics



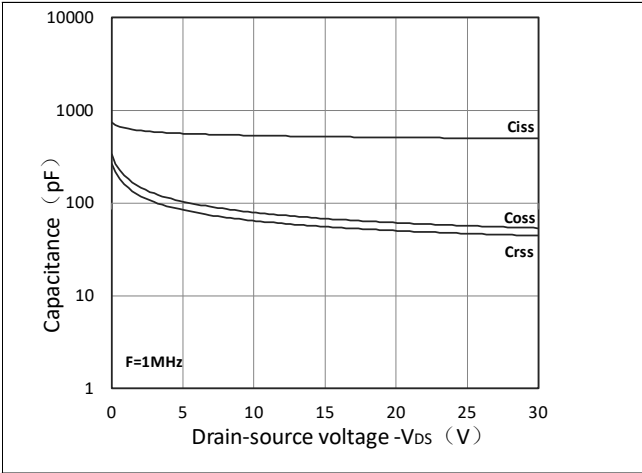


Figure 7. Capacitance Characteristics

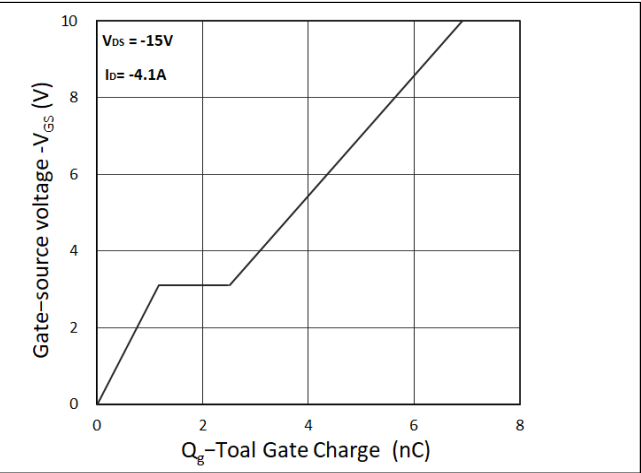


Figure 8. Gate Charge Characteristics

Outline Drawing – SOT-23

PACKAGE OUTLINE

SOT-23

SYMBOL	MILLIMETER		INCHES	
	MIN	MAX	MIN	MAX
A	0.90	1.15	0.035	0.045
A1	0.00	0.10	0.000	0.004
b	0.30	0.50	0.012	0.020
c	0.08	0.15	0.003	0.006
D	2.80	3.00	0.110	0.118
E	2.25	2.55	0.089	0.100
E1	1.20	1.40	0.047	0.055
e	0.95 BSC		0.037BSC	
e1	1.80	2.00	0.071	0.079
L	0.55REF		0.022REF	
θ	0°	8°	0°	8°

DIMENSIONS		
DIM	INCHES	MILLIMETERS
M	0.080	2.02
C	0.032	0.80
Z	0.111	2.82
e	0.037 BSC	0.95 BSC
e1	0.075 BSC	1.90 BSC
b	0.032	0.80

Notes

1. Dimensioning and tolerances per ANSI Y14.5M, 1985.
2. Controlling Dimension: Inches
3. Pin 3 is the cathode (Unidirectional Only).
4. Dimensions are exclusive of mold flash and metal burrs.

Marking Codes

Part Number	WM03P41M
Marking Code	

Package Information

Qty: 3k/Reel

CONTACT INFORMATION

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For additional information, please contact your local Sales Representative.

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Specifications are subject to change without notice.
The device characteristics and parameters in this data sheet can and do vary in different applications and actual device performance may vary over time.
Users should verify actual device performance in their specific applications.